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RbPbPS₄: a promising IR nonlinear optical material achieved by lone-pair-cation-substitution-induced structure transformation†

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When stereochemically-active-lone-pair (SCALP) cations are introduced into chalcogenide systems, it is beneficial to produce a remarkable second-harmonic generation (SHG) response ($d_{\rm eff}$), but it also causes a narrow band gap ($E_{\rm g}$), which ultimately results in negative two-photon and free-carrier absorption. Hence, how to obtain a wide $E_{\rm g}$ (>2.33 eV) while maintaining a strong $d_{\rm eff}$ remains a significant challenge in this domain. In this work, Rb is partially replaced by SCALP Pb in the known ternary centrosymmetric (CS) Rb₃PS₄ (space group: Pnma). This results in a quaternary non-centrosymmetric (NCS) RbPbPS₄ (space group: $P2_12_12_1$), which possesses distinct 2D [PbPS₄]⁻ layers and Rb⁺ occupies the interlayer spaces as the counter cations. Notably, RbPbPS₄ exhibits a promising overall performance, including strong $d_{\rm eff}$ (2.5 × AgGaS₂), wide IR transmittance cutoff edge (up to 18.1 μ m) along with the large $E_{\rm g}$ (2.75 eV), resulting in an improved laser-induced damage threshold (7.5 × AgGaS₂). Theoretical calculations further indicated that the favorable balance between strong $d_{\rm eff}$ and large $E_{\rm g}$ in RbPbPS₄ can be attributed to the synergies of the [PbS₇] and [PS₄] nonlinear optical (NLO)-active units. This study not only presents a high-performance Pb-based IR-NLO candidate but also underscores the effectiveness of partial substitution of SCALP cations in inducing a CS-to-NCS structural transformation.

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Introduction

Nonlinear optical (NLO) materials have garnered unprecedented attention in laser science and technology because of their ability to facilitate frequency conversion in solid-state laser devices. As widely recognized, an excellent NLO candidate should meet several crucial prerequisites: a sufficient second-harmonic generation (SHG) intensity ($d_{\rm eff}$), a large energy gap ($E_{\rm g}$), a wide optical transparent window, a moderate birefringence (Δn), chemical stability, and availability for

obtaining large single crystals.2 In the infrared (IR) region,

In addition to the performance prerequisites mentioned above, a prerequisite of an IR-NLO crystal is that it has a non-centrosymmetric (NCS) structure.⁶ The addition of stereochemically-active-lone-pair (SCALP) cations, like As³⁺, Sb³⁺, Bi³⁺, Sn²⁺, and Pb²⁺, to chalcogenide systems has attracted the most attention among all the feasible approaches for creating IR-NLO materials because the majority of these chalcogenides exhibit exceptional IR-NLO performances.⁷ Among these

and theory results, together with additional tables and figures. CCDC 2347371. For ESI and crystallographic data in CIF or other electronic format see DOI: https://doi.org/10.1039/d4qi01040j

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numerous vital fields, including optoelectronic instruments, resource exploration, and remote laser communication, has sparked widespread attention and interest. Despite the strong $d_{\rm eff}$ exhibited by commercial IR-NLO crystals such as AgGaQ₂ (Q = S, Se)³ and ZnGeP₂,⁴ which make them suitable for applications in the IR region, they still suffer from limitations in high-power laser systems due to their low laser-induced damage thresholds (LIDT) or detrimental two-photon absorption, primarily attributed to their small $E_{\rm g}$. However, integrating these optical performances into a single crystal is extremely challenging because they typically depend on competing structural requirements, such as the trade-off between wide $E_{\rm g}$ and strong $d_{\rm eff}$. Therefore, it is of scientific and technological significance to explore new IR-NLO crystals with outstanding comprehensive performance to overcome these challenges.

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cations, Pb^{2+} makes a significant contribution to the $d_{\rm eff}$ but adversely affects the optical E_g .⁸ As is known, narrow energy gaps (E_g < 2.33 eV) are unable to mitigate some harmful twophoton or free-carrier absorption under fundamental 1064 nm laser sources. Therefore, achieving a wide E_g (>2.33 eV) while maintaining a strong d_{eff} remains a significant challenge in Pb-based IR-NLO material design. On the other hand, partial chemical substitution in view of known centrosymmetric (CS) parent structures has shown to be a straightforward but incredibly successful approach in recent years for the design and synthesis of novel high-performance SCALP-based IR-NLO crystals. 10 Successful examples include NCS Ba2As2Se5 (parent structure: CS Ba₂GaAsSe₅), ¹¹ NCS K₂Ag₃Sb₃S₇ (parent structure: CS $K_2Sb_4S_7$, ¹² NCS $ABiP_2S_6$ (A = K, Rb) (parent structure: CS $A_4P_2S_6$, ^{13,14} NCS $Sn_7Br_{10}S_2$ (parent structure: CS $SnBr_2$), ¹⁵ Sr_{2-x}Pb_xGeSe₄ (parent structure: NCS Sr₂GeSe₄), ¹⁶ and NCS Pb₄SeBr₆ (parent structure: CS PbBr₂).¹⁷ Considering these

factors, our focus lies in identifying suitable CS parent structures with wide E_g and achieving CS-to-NCS structural transformation by introducing SCALP Pb for partial chemical substitution. This approach aims to obtain NCS materials with excellent, well-balanced IR-NLO performance.

The ternary chalcophosphate Rb₃PS₄ has piqued our interest due to its CS space group of Pmna and unique zero-dimensional (0D) cluster structure. 18 By incorporating distorted Pbbased motifs, it is possible to disrupt symmetric centers, leading to structural reconstruction and the formation of NCS compounds. Furthermore, Rb₃PS₄ boasts a sufficiently large E_{σ} (>3.5 eV), which can help offset the potential decrease in E_{g} resulting from the introduction of SCALP Pb2+ cations into new compounds. Following this approach, we have designed and synthesized the quaternary Pb-based thiophosphate RbPbPS₄, featuring a two-dimensional (2D) layered structure composed of [PbS₇] polyhedra and [PS₄] tetrahedra.

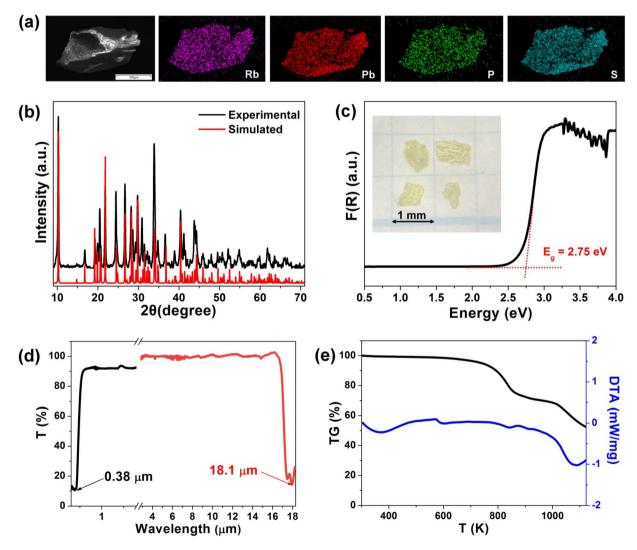


Fig. 1 Experimental characterization results of PbPbPS₄: (a) SEM image and corresponding elemental distribution maps; (b) experimental (black) and simulated (red) powder XRD patterns; (c) UV-vis-NIR spectrum (inset: photograph of the title crystals); (d) optical transmittance spectrum; (e) TG-DTA test curves.

Remarkably, RbPbPS₄ demonstrates comprehensive IR-NLO performance, including a strong d_{eff} (3.2 times that of AgGaS₂), one of the widest E_g among Pb-based NCS chalcogenides, high LIDT (7.5 times that of AgGaS₂), a broad transmittance range (up to 18.1 μ m), and suitable Δn (0.112@2050 nm). In this report, we provide detailed insights into the CS-to-NCS structural transformation and the related optical properties of RbPbPS₄. Additionally, theoretical calculations are employed to further elucidate its linear optical and NLO performances.

Results and discussion

There are reports of RbPbPS₄'s crystal structure exhibiting two distinct phases. 19 However, we meticulously determined the structure of the title compound to explore the intricate relationship between its NCS crystal structure and NLO properties. Light yellow lamellar crystals of RbPbPS4, with sizes reaching the millimeter level, were grown using a simple boron-chalcogen method.20 This method differs from previously reported techniques, which often necessitate complex

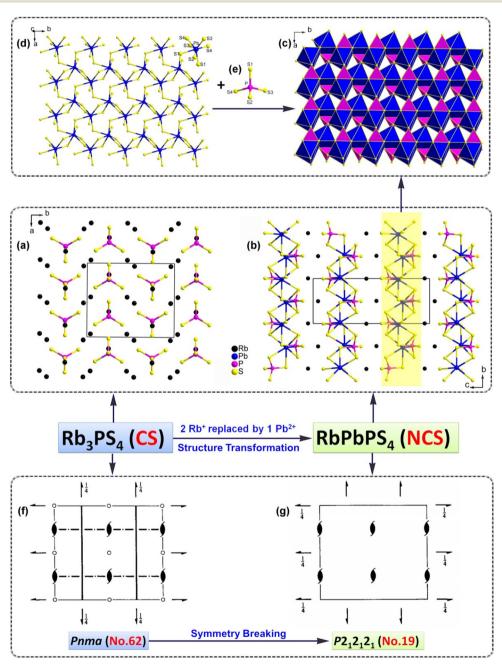


Fig. 2 Structure evolution from ternary CS Rb₃PS₄ to quaternary NCS RbPbPS₄: view of the 2D layered structures of (a) Rb₃PS₄ and (b) RbPbPS₄ along the ab and bc plane, respectively; (c) a polyhedral 2D layer [PbPS₄] composed of (d) 2D Pb-S layer and (e) discrete tetrahedral [PS₄] motifs; (f and g) spatial symmetry operation changing from CS Pmna (no. 62) to NCS P2₁2₁2₁ (no. 19).

experimental procedures or involve the use of costly and hazardous elemental Rb as a raw material. Elemental distribution maps indicate that Rb, Pb, P, and S are uniformly distributed throughout the crystals (Fig. 1a). Furthermore, EDX results confirmed that the average molar ratios of the title compound correspond to the formula determined by single-crystal XRD analysis (Fig. S1†). Powder XRD testing validated the phase purity of the title compound, as the experimental patterns closely matched the simulated data obtained from singlecrystal XRD analyses (Fig. 1b). The UV-vis diffuse reflectance spectrum of RbPbPS4 is depicted in Fig. 1c, and absorption data were derived using the Kubelka-Munk equation.²¹ With an experimental optical E_g of 2.75 eV, RbPbPS₄ exhibits the second-highest recorded value among Pb-based IR-NLO chalcogenides. Additionally, RbPbPS4 demonstrates broad optical transparency across the 0.38-18.1 µm range (Fig. 1d). Thermogravimetric-differential thermal analysis (TG-DTA) was employed to assess the thermal stability of RbPbPS4, revealing that the compound remains stable below 700 K (Fig. 1e).

In the asymmetric unit, ternary Rb₃PS₄ has two independent Rb atoms (Wyckoff positions: 4c and 8d), one independent P atom (Wyckoff position: 4c), and two independent S atoms (Wyckoff positions: 4c and 8d). The P^{5+} cation is located in the center of its common tetrahedron, with P-S bond lengthes ranging from 2.043 to 2.055 Å and the bond angles in the range of 108.82-111.48°. Ternary Rb₃PS₄ belongs to the orthorhombic system [space group: Pnma (no. 62)] and the crystal structure consists of counterbalanced Rb⁺ cations situated in between discrete tetrahedral [PS₄] basic building units (BBUs) aligned parallel in opposing orientations (Fig. 2a). Unfortunately, Rb₃PS₄ lacks NLO activity due to its CS crystal structure.

Quaternary RbPbPS4 adopts the NCS orthorhombic space group P2₁2₁2₁ (no. 19, Table S1†), according to single-crystal XRD investigation. The cell lattice possesses dimensions of a =6.3981(2) Å, b = 6.6888(2) Å, c = 17.2823(5) Å, and V = 739.61(4) \mathring{A}^3 . These crystal parameters are in good agreement with the NCS phase that was previously published. The compound has a 2D layered structure with discrete counterbalanced Rb⁺ cations inserted in the channels that are arranged in an "ABABAB" mode perpendicular to the ab-plane (Fig. 2b and c). With seven S atoms polyhedral coordinating each Pb atom in the structure, the highly distorted [PbS₇] BBUs with Pb-S bond lengths of 2.916-3.281 Å are formed. As shown in Fig. 2d, adjacent [PbS₇] BBUs are joined by apex-sharing S atoms to generate a 2D Pb-S layer. While the P-S bonds in RbPbPS4 range in length from 2.031 to 2.069 Å and in bond angles from 106.56 to 111.62°, each P atom is comparable to that of Rb₃PS₄ and is encircled by four S atoms, forming the deformed [PS₄] tetrahedron (Table S2†). Subsequently, apex-sharing between these 2D Pb-S layers (Fig. 2d) and distinct [PS₄] BBUs (Fig. 2e) progressively linked them, resulting in the formation of a 2D [PbPS₄] anionic layer (Fig. 2c).

Fig. 2 shows the CS-to-NCS structural evolution via partial SCALP cation substitution from ternary CS Rb₃PS₄ to quaternary NCS RbPbPS₄. From a structural perspective, the following noteworthy modifications have been made following the partial replacement of Rb by SCALP Pb. First off, the initial highly symmetric structure is broken by the addition of SCALP [PbS₇] BBUs and the reassembly of discrete [PS₄] BBUs, which

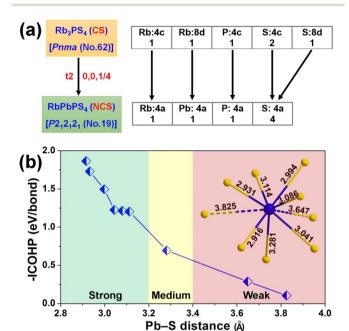


Fig. 3 (a) Group-subgroup relations between CS Rb₃PS₄ [space group: Pmna (no. 62)] and NCS RbPbPS₄ [space group: $P2_12_12_1$ (no. 19)]; (b) crystal orbital Hamilton population (COHP) curves for the Pb-S bond length in RbPbPS4 (the inset figure is the coordination geometry of Pb atom).

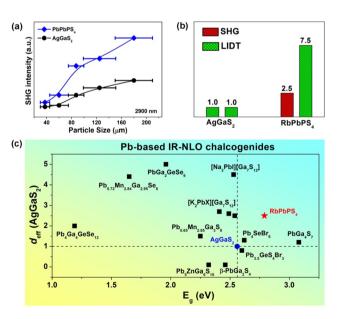


Fig. 4 (a) SHG intensities vs. particle size at $\lambda = 2900$ nm for PbPbPS₄ and AgGaS2; (b) the relative SHG and LIDT intensities of PbPbPS4 and reference commercial material AgGaS2 in the particle size of 150-210 μ m; (c) comparison of d_{eff} (xAgGaS₂) and E_{q} (eV) of reported Pb-based IR-NLO chalcogenides.

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convert the 0D cluster structure into a 2D layered structure. Fig. 2f and g show the detailed symmetric operation modifications that occur after the substitution of SCALP Pb²⁺ cations, resulting in the removal of all center sites and the realization of the CS-to-NCS structural evolution. In particular, space group *Pnma* (no. 62) converts to $P2_12_12_1$ (no. 19) from the Bärnighausen tree via a translationengleiche reduction in index 2's symmetry (Fig. 3a).²² When Pb is substituted for Rb, the atomic positions (4c and 8d) in Rb₃PS₄ become 4a in RbPbPS₄ (see Table S3† for details). To put it briefly, the novel compound that was produced, RbPbPS4, has good structural anisotropy, which helps to get a higher Δn for achieving PM feature. Secondly, the coordination number (CN) of the two crystallographically independent Rb atoms in Rb3PS4 differ (CN = 8 for Rb1 and CN = 9 for Rb2), but are identical in RbPbPS₄ (CN = 11) with Rb-S bond distances less than 4.4 Å (refer to Fig. S2 and S3 in ESI†). Finally, considering the flexible CN of Pb²⁺ cations, the integrated crystal orbital Hamilton population (ICOHP) curve was examined.²³ As depicted in Fig. 3b, it is evident that the short Pb-S bond lengthes of 2.916-3.114 Å exhibit stronger bonding interactions compared

to the long Pb-S bond lengthes (3.647-3.825 Å), while the Pb-S bond distance of 3.281 Å falls between them, representing a medium interaction (see Table S2† for details). Based on the above analysis, it is reasonable to infer that the Pb atom forms a [PbS₇] mono-capped triangular prism. Research on the distinct [PbS₇] coordination mode in NCS chalcogenides is notably lacking, and a seven-coordinated example of this has been reported in Pb5Ga6ZnS15.8d Pb2+ cations in NCS chalcogenides are mostly five-coordinated (as in [Na₂PbI][Ga₇S₁₂]^{8f}) six-coordinated (as Pb₄Ga₄GeS₁₂ ^{8a} in Pb_{0.65}Mn_{2.85}Ga₃S₈^{8b}), among other compounds that have been found.

Furthermore, through comparison with known ternary and quaternary chalcophosphates, it is determined that substituting SCALP Pb for partial alkali metal Rb is the most optimal and rational structural approach to accomplish the CS-to-NCS structural transformation of template structure Rb₃PS₄. Fig. S4† provides a detailed structural evolution. Roughly speaking, these replacements fall into three categories. In the first, three Rb atoms are completely substituted by one trivalent element or three monovalent elements in the absence of

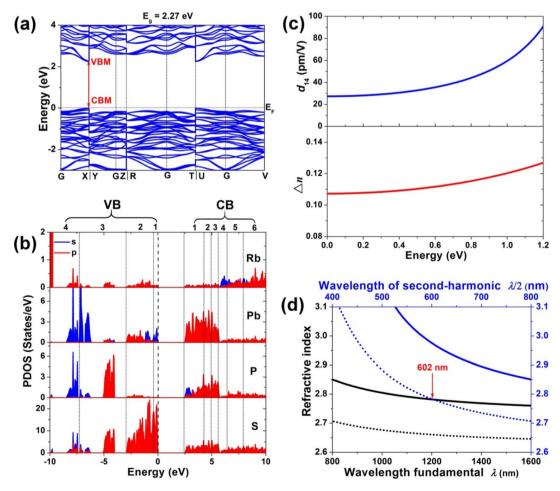


Fig. 5 Theoretical results of electronic structures and optical parameters of PbPbPS_a: (a) band structure; (b) partial density of states; (c) calculated nonzero independent SHG coefficient d_{14} (pm V⁻¹) and calculated birefringence (Δn); (d) calculated refractive index dispersion curves with the shortest type-I PM cut-off wavelength.

SCALP components. CS structures are displayed by the resultant compounds, including REPS₄ (space group: I4₁/acd),²⁴ BPS₄ (space group: *Ibam*), ²⁵ GaPS₄ (space group: $P2_1/c$), ²⁶ and Tl₃PS₄ (space group: Pnma).²⁷ The second category entails complete substitution of SCALP elements, as seen in SbPS₄ (space group: $P\bar{1}$)²⁸ and BiPS₄ (space group: *Ibca*), ²⁹ which also belong to the CS structures. The third category involves partial substitution, where Rb is partially replaced by monovalent or divalent elements. The resulting compounds, such as Rb₂AgPS₄ (space group: P1), 30 RbAg₅P₂S₈ (space group: Pbca), 31 RbSrPS₄ (space group: Pnma),³² RbBaPS₄ (space group: Pnma),³³ RbPdPS₄ (space group: I4/mcm),³⁴ and RbHgPS₄ (space group: $P2_1/n$, 35 all adopt CS structures. Therefore, it is reasonable to replace partial Rb with SCALP elements to realize a structural transition from CS Rb₃PS₄ to NCS RbPbPS₄. Hence, employing established CS chalcophosphates as the parent structure and partially substituting them with SCALP-cation groups proves to be an effective chemical strategy for accomplishing the CS-to-NCS structural evolution.

As RbPbPS₄ belongs to the NCS space group P2₁2₁2₁ and possesses the NLO-active motifs [PbS₇] and [PS₄], a relatively

strong d_{eff} could be expected. Powder SHG testing for RbPbPS₄ was conducted using the modified Kurtz-Perry technology, 35 with irradiation from a 2900 nm laser and commercial material AgGaS₂ as a reference. As depicted in Fig. 4a, the positive correlation between the particle size and SHG intensity indicates that RbPbPS4 exhibits PM behavior. The SHG intensity of RbPbPS₄ is approximately 2.5 times that of benchmark AgGaS₂ in a particle size range of 150-210 µm (Fig. 4b). Based on $d_{\text{eff}} = d_{\text{eff},R} (I^2 \omega / I_R^2 \omega)^{1/2} (d_{\text{eff},R} = 13.4 \text{ pm V}^{-1} \text{ for AgGaS}_2),$ the effective SHG coefficient d_{eff} of RbPbPS₄ at 2900 nm is 21.2 pm V⁻¹. In addition, powder LIDT measurement was employed to preliminarily evaluate the LIDT value, 36 with the increased optical E_g suggesting that the title crystal would exhibit higher LIDT. As illustrated in Fig. 4b, the LIDT of RbPbPS₄ (10.88 MW cm⁻²) is estimated to be 7.5 times that of AgGaS₂ (1.45 MW cm⁻²) under the same testing conditions. Compared with other reported Pb-based IR-NLO materials (Fig. 4c and Table S4†), RbPbPS₄ demonstrates a favorable balance between strong $d_{\rm eff}$ and large $E_{\rm g}$. Notably, RbPbPS₄ represents the first quaternary Pb-based chalcogenide to overcome the incompatibility between a wide E_g (>2.56 eV, the E_g of AgGaS₂) and a

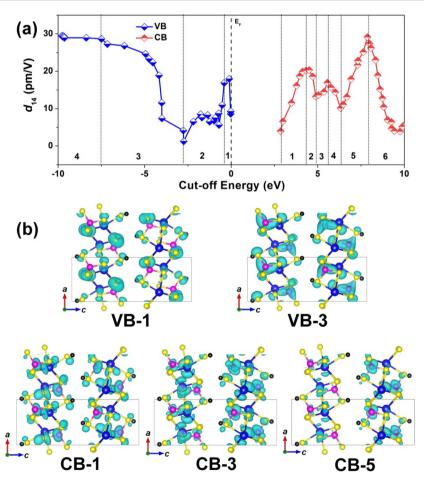


Fig. 6 Theoretical analysis of the intrinsic mechanism of SHG source for PbPbPS₄: (a) cut-off energy (eV) dependence of the static d₁₄ (pm V⁻¹); (b) distribution of the partial charge density maps with major contributions in the VB-1, VB-3, CB-1, CB-3 and CB-5 regions. Black atoms: Rb; blue atoms: Pb; pink atoms: P; yellow atoms: S.

sufficient $d_{\rm eff}$ (>1.0 × AgGaS₂). This balance IR-NLO performance can be compared to the recently reported quaternary NCS chalcogenides, such as α -Li₂ZnGeS₄, ³⁷ Li₄CdSn₂S₇, ³⁸ NaMg₃Ga₃S₈, ³⁹ and (CuI)₃P₄S₄. ⁴⁰

To gain further insights into the underlying structure-property relationship of the title compound, systematic theoretical calculations were conducted, encompassing band structure, densities of states (DOSs), and linear optical and NLO parameters, based on DFT. The calculated electronic band structure reveals a direct E_g of 2.27 eV for RbPbPS₄, as the valence band maximum (VBM) and conduction band minimum (CBM) coincide at the same high-symmetry k-points (Fig. 5a). The smaller calculated E_g can be attributed to underestimation by the DFT calculation. 41 The partial DOSs of RbPbPS4 are depicted in Fig. 5b, indicating that the tops of the VBs are predominantly composed of S-3p states, with a minor contribution from Pb-5s and P-3p states, while the bottoms of the CBs primarily consist of S-3p, Pb-5p, P-3s/3p, and Rb-5p states. Furthermore, the NLO coefficients of RbPbPS4 can be calculated according to the electronic structure. In the light of Kleinman symmetry, 42 RbPbPS4 exhibits only one nonzero independent SHG coefficient, $d_{14} = 31.8 \text{ pm V}^{-1}$ at 2900 nm (ca. 0.43 eV) (Fig. 5c). Furthermore, the calculated d_{eff} of RbPbPS₄ is 26.88 pm V⁻¹, under 2900 nm irradiation,³⁵ which essentially coincides with the experimental findings. Additionally, the calculated Δn value of RbPbPS₄ is 0.109 at 2900 nm, significantly surpassing that of AgGaS₂ ($\Delta n \sim 0.04$).⁴³ This suggests that RbPbPS4 may be well-suited to achieve the PM condition for the SHG process. Furthermore, the line refractive dispersion diagrams indicate that the shortest type-I phase-matched output wavelength is 602 nm (Fig. 5d). 44

To visually illustrate the contribution of the constituent BBUs to the SHG effect, the cutoff energy dependence of the static d_{14} for RbPbPS₄ is calculated using a length-gauge formalism method. As depicted in Fig. 6a, the d_{14} values exhibit an upward trend in the VB-1, VB-3, CB-1, CB-3, and CB-5 intervals. This illustrates that the orbitals in these regions have a significant influence on the overall NLO response. Moreover, by integrating the partial DOSs (Fig. 5b) with the relevant partial charge density maps (Fig. 6b), it is evident that the enhancement of the $d_{\rm eff}$ in RbPbPS₄ primarily stems from the strong hybridization of electron states at the top of the VBs and the substantial distortion of [PbS₇] and [PS₄] groups, indicative of the 2D [PbPS₄] alternating arrangement layer.

Conclusions

In summary, building upon the parent ternary CS compound Rb_3PS_4 , we implemented a strategy involving the partial substitution of Rb with SCALP Pb, resulting in the creation of a new quaternary NCS chalcophosphate, RbPbPS₄. This substitution also triggered a structural transformation from 0D clusters to 2D layers. As anticipated, experimental findings highlight RbPbPS₄ as a promising candidate for IR-NLO applications, boasting a large $d_{\rm eff}$ (2.5 × AgGaS₂ at 2900 nm), a broad trans-

mittance cutoff window (0.38–18.1 μ m), and a significant E_g (2.75 eV) conducive to a high LIDT (7.5 × AgGaS₂ at 1064 nm). Detailed structure–property analyses elucidate that the strong calculated $d_{\rm eff}$ (26.88 pm V⁻¹@2900 nm) and large calculated birefringence (0.109@2900 nm) in RbPbPS₄ primarily stem from the cooperative effects of [PbS₇] and [PS₄] NLO-active motifs. These findings underscore the efficacy of the lone-paircation substitution strategy in achieving both structural transformation and effectively balancing strong $d_{\rm eff}$ with a large E_g in SCALP-based chalcogenides.

Author contributions

A-Yang Wang: investigation, formal analysis, writing – original draft. Sheng-Hua Zhou: investigation, methodology, validation. Mao-Yin Ran: investigation, formal analysis, validation. Bingxuan Li: formal analysis, validation. Xin-Tao Wu: conceptualization, writing – review & editing. Hua Lin: supervision, conceptualization, writing – review & editing. Qi-Long Zhu: supervision, writing – review & editing.

Conflicts of interest

There are no conflicts to declare.

Acknowledgements

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